

YJ Planar Schottky Barrier Diode Die Specification

60V 10A, 87mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB087M060AS-280A

Main Products Characteristics

~ A_F = 10 A
~ Max. T_b = 150 °C
~ ESD: >8KV, IEC61000-4-2 (C)
~ T_j = 100 °C

Maximum Ratings

Static Electrical Characteristics (T_a = 25°C)

I_F = 10 A
P_{tot} = 300 mW, ±2%

Device Schematics and Outline Drawing

Die Thickness *
Die Size **